**Product data sheet** 

## 1. General description

WMS20N270SK is a high performance super logic level N-channel MOSFET in SOT23 package, which utilizes advanced Trench MOSFET technology to provide low  $R_{\rm DS(on)}$  and gate charge. It is designed and qualified in a wide range of industrial and consumer applications.



### 2. Features and benefits

- Advance High Cell Density Trench Technology
- Low R<sub>DS(on)</sub> to Minimize Conduction Losses
- Low Capacitance to Minimize Switching Losses
- Optimized Gate Charge to Minimize Driver Losses
- · RoHS Compliant, Halogen Free and Lead Free

## 3. Applications

- Load Switch
- General PWM Applications

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit
Absolute	maximum rating						
V <sub>DS</sub>	drain-source voltage				20		V
$V_{GS}$	gate-source voltage				±10		V
I <sub>D</sub>	continuous drain current	V <sub>GS</sub> = 4.5 V; T <sub>a</sub> = 25 °C			6		Α
P <sub>tot</sub>	power dissipation	T <sub>a</sub> = 25 °C		1.4		W	
T <sub>j</sub>	junction temperature			-55 to 150		°C	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
R <sub>DS(on)</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}, I_D = 5.7 \text{ A}$		-	20	27	mΩ
	resistance	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 3 A		-	28	44	mΩ
Dynamic (	characteristics						
Q <sub>G(tot)</sub>	total gate charge	$I_D = 5.7 \text{ A}; V_{DS} = 10 \text{ V}; V_{GS} = 4.5 \text{ V}$		-	5.3	-	nC

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	2	D
2	S	source	3 □	
3	D	drain	1 2	Sym300 S

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WMS20N270SK	SOT23	WMS20N270SKX	Reel	3000	SOT23L	22-Aug-2022

# 7. Marking

Table 4. Marking codes

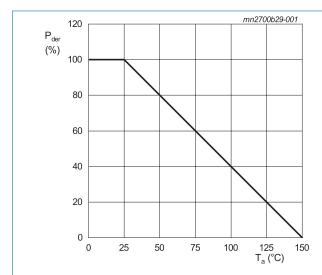
Type number	Marking codes
WMS20N270SK	AD

# 8. Limiting values

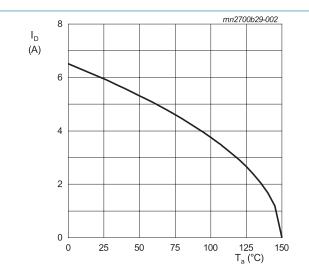
### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V <sub>DS</sub>	drain-source voltage			20	V
$V_{GS}$	gate-source voltage			±10	V
I <sub>D</sub>	continuous drain current	V <sub>GS</sub> = 4.5 V; T <sub>a</sub> = 25 °C		6	Α
		V <sub>GS</sub> = 4.5 V; T <sub>a</sub> = 70 °C		4.8	Α
I <sub>DM</sub>	pulsed drain current	t <sub>p</sub> = 10 μs; T <sub>a</sub> = 25 °C		24	Α
P <sub>tot</sub>	power dissipation	T <sub>a</sub> = 25 °C		1.4	W
T <sub>stg</sub>	storage temperature			-55 to 150	°C
T <sub>j</sub>	junction temperature			-55 to 150	°C



P<sub>der</sub> = (P<sub>tot</sub> / P<sub>tot(25 °C)</sub>) x 100% Fig. 1. Normalized total power dissipation as a function of ambient temperature



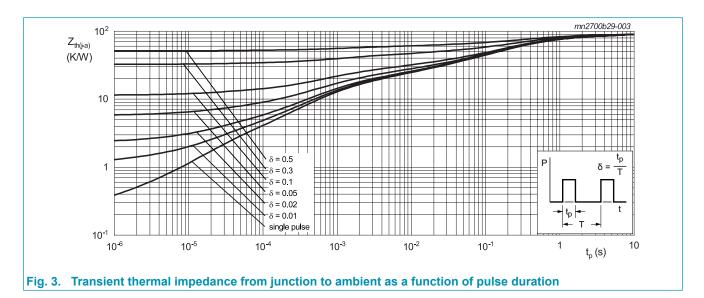
V<sub>GS</sub> = 4.5 V
Fig. 2. Continuous Drain Current as a function of ambient temperature

### 9. Thermal & Mechanical characteristics

**Table 6. Thermal & Mechanical characteristics** 

S	ymbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R	$R_{th(j-a)}$	thermal resistance	t ≤ 10s	[1]	-	72	90	K/W
	from junction to ambient	in free air	[1]	-	95	120	K/W	

[1] Surface mount on FR4 board of 1 inch2, 1 oz copper.



## 10. Characteristics

### **Table 7. Characteristics**

T<sub>i</sub> = 25 °C unless otherwise noted

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	racteristics		,			'	
$V_{(BR)DSS}$	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V		20	-	-	V
$V_{\text{GS(th)}}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$		0.5	0.7	1.1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V		-	-	1	μA
		V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C		-	-	10	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = \pm 10 \text{ V}; V_{DS} = 0 \text{ V}$		-	-	±100	nA
R <sub>DS(on)</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 5.7 A		-	20	27	mΩ
	resistance	V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 3 A		-	28	44	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz		-	3.3	-	Ω
Dynamic	characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 5.7 \text{ A}; V_{DS} = 10 \text{ V}; V_{GS} = 4.5 \text{ V}$		-	5.3	-	nC
Q <sub>GS</sub>	gate-source charge			-	0.7	-	nC
$Q_{GD}$	gate-drain charge			-	1.7	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; V <sub>GS</sub> = 0 V; f = 1 MHz		-	381	-	pF
C <sub>oss</sub>	output capacitance			-	77	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	69	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 10 \text{ V}; V_{GS} = 4.5 \text{ V}; R_G = 6 \Omega;$		-	7.1	-	ns
t <sub>r</sub>	rise time	$I_{D} = 5.7 A$		-	14	-	ns
$t_{d(off)}$	turn-off delay time			-	25	-	ns
t <sub>f</sub>	fall time			-	13	-	ns
Source-d	rain diode						
$V_{SD}$	source-drain voltage	V <sub>GS</sub> = 0 V; I <sub>S</sub> = 1 A		-	0.7	1	V
		V <sub>GS</sub> = 0 V; I <sub>S</sub> = 1 A; T <sub>j</sub> = 125 °C		-	0.57	-	V
Is	body-diode continuous current	T <sub>a</sub> = 25 °C		-	-	2	А
t <sub>rr</sub>	reverse recovery time	$V_{GS} = 0 \text{ V}; I_S = 5.7 \text{ A}; \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		-	13	-	ns
Q <sub>rr</sub>	reverse recovered charge			-	3.2	-	nC
I <sub>rrm</sub>	reverse recovery current			-	0.4	-	Α

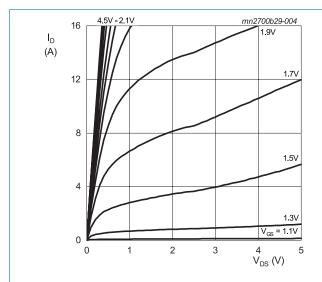
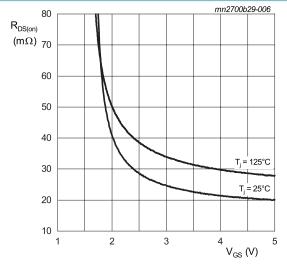
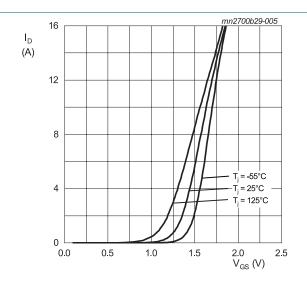


Fig. 4. Drain current as a function of drain-source voltage; typical values



V<sub>GS</sub> = 4.5 V; I<sub>D</sub> = 5.7 A

Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



V<sub>DS</sub> = 5 V
Fig. 5. Drain current as a function of gate-source voltage; typical values

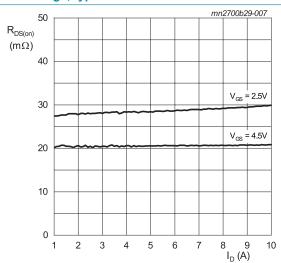
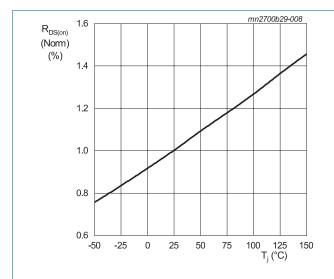
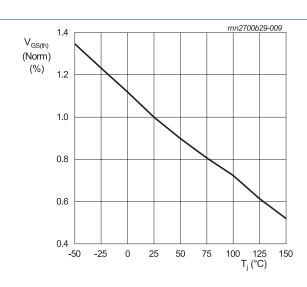


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values



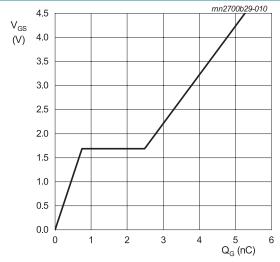
 $V_{GS}$  = 4.5 V;  $I_{D}$  = 5.7 A

Fig. 8. Normalized drain-source on-state resistance as a function of junction temperature

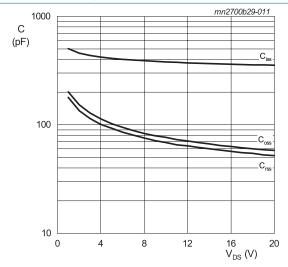


 $V_{GS}$  =  $V_{GS}$ ;  $I_D$  = 250  $\mu A$ 

Normalized gate-source threshold voltage as a Fig. 9. function of junction temperature

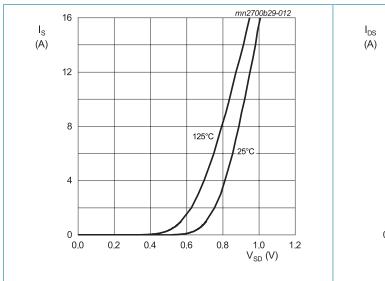


 $I_D = 5.7 \text{ A}; V_{DS} = 10 \text{ V}$ Fig. 10. Gate-source voltage as a function of gate charge; typical values

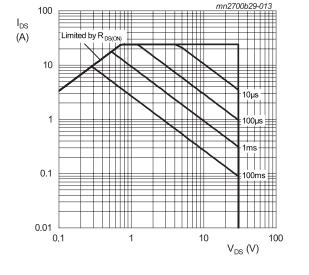


 $V_{GS} = 0 V$ ; f = 1 MHz

Fig 11. Capacitances as a function of drain-source voltage; typical values

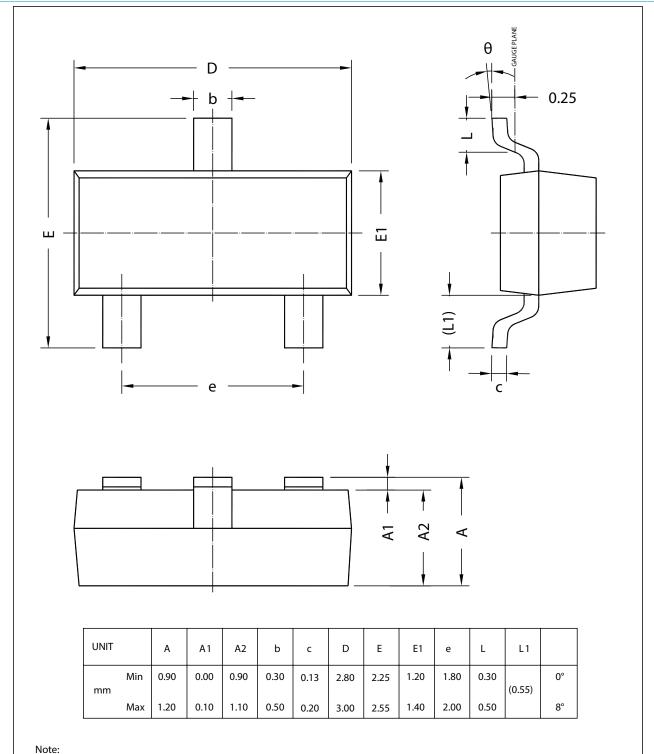


V<sub>GS</sub> = 0 V
Fig 12. Source current as a function of source-drain voltage; typical values



T<sub>a</sub> = 25 °C Fig. 13. Safe operating area

# 11. Package outline



Note:

1. All dimensions don't include mold flash and metal protrusion.

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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